

isc N-Channel MOSFET Transistor

2SK1503

DESCRIPTION

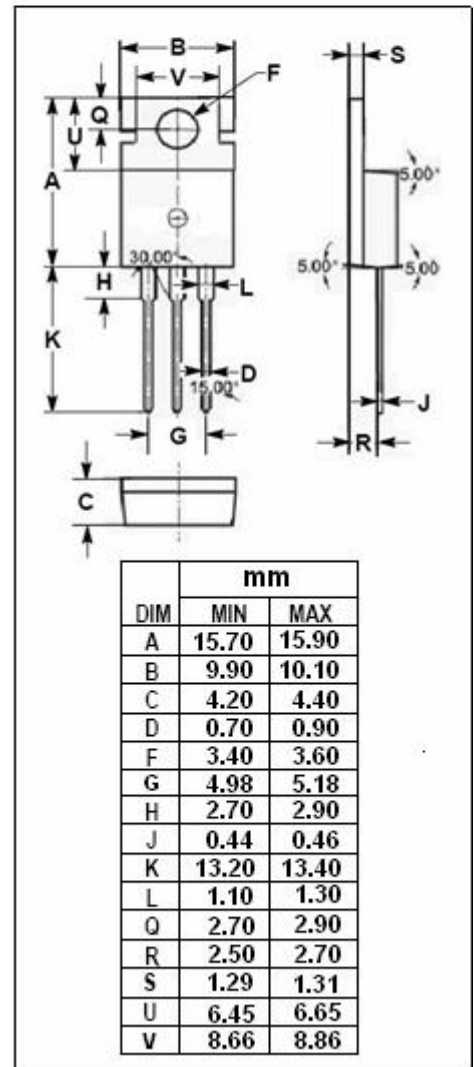
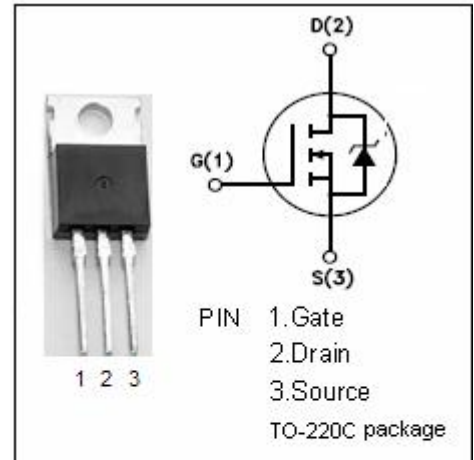
- Drain Current $-I_D=10A @ T_C=25^\circ C$
- Drain Source Voltage-
: $V_{DSS}=500$ (Min)

APPLICATIONS

- Designed especially for high voltage,high speed applications, such as off-line switching power supplies , UPS,AC and DC motor controls,relay and solenoid drivers.

ABSOLUTE MAXIMUM RATINGS($T_a=25^\circ C$)

SYMBOL	ARAMETER	VALUE	UNI T
V_{DSS}	Drain-Source Voltage ($V_{GS}=0$)	500	V
V_{GS}	Gate-Source Voltage	± 30	V
I_D	Drain Current-continuous@ $TC=25^\circ C$	10	A
P_{tot}	Total Dissipation@ $TC=25^\circ C$	80	W
T_j	Max. Operating Junction Temperature	150	$^\circ C$
T_{stg}	Storage Temperature Range	-55~150	$^\circ C$



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• ELECTRICAL CHARACTERISTICS (T_C=25°C)

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP	MAX	UNIT
V _{(BR)DSS}	Drain-Source Breakdown Voltage	V _{GS} =0; I _D = 1mA	500			V
V _{GS(th)}	Gate Threshold Voltage	V _{DS} =0; I _D =1mA	2.5	3.5	5.0	V
R _{DS(on)}	Drain-Source On-stage Resistance	V _{GS} =10V; I _D =5A		0.7	0.9	Ω
I _{GSS}	Gate Source Leakage Current	V _{GS} = ±30V; V _{DS} = 0			± 100	nA
I _{DSS}	Zero Gate Voltage Drain Current	V _{DS} =500V; V _{GS} = 0			500	uA
V _{SD}	Diode Forward Voltage	I _F =10A; V _{GS} =0		1.10	1.65	V
t _r	Rise time	V _{GS} =10V; I _D =10A; R _L =25 Ω		35		ns
t _{on}	Turn-on time			50		ns
t _f	Fall time			65		ns
t _{off}	Turn-off time			265		ns